

N-Channel 30-V (D-S) MOSFET

Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low RDS(on) and to ensure minimal power loss and heat dissipation.

Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

Features

- Low rDS(on) Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications
- RoHS compliant package

Package type: SO-8

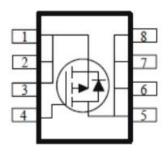
Packing & Order Information

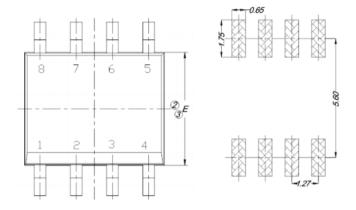
3,000/Reel

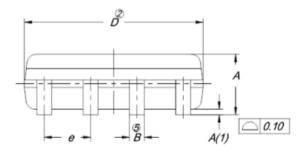


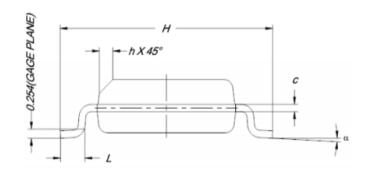
RoHS COMPLIANT

Graphic symbol









DIM	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
Α	1.35	1.55	1.75	
A(1)	0.10	0.18	0.25	
В	0.38	0.45	0.51	
С	0.19	0.22	0.25	
D	4.80	4.90	5.00	
E	3.80	3.90	4.00	
е	1.27 BSC			
Н	5.80	6.00	6.20	
L	0.50	0.72	0.93	
α	0°	4°	8°	
h	0.25	0.38	0.50	



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T _A =25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V_{DS}	Drain-Source Voltage	30	V		
V _{GS}	Gate-Source Voltage	±20	V		
I_D	Continuous Drain Current ^a (T _A =25°C)	±6.9	A		
	Continuous Drain Current ^a (T _A =70°C)	±5.6	A		
I_{DM}	Pulsed Drain Current ^b	±40	A		
Is	Continuous Source Current (Diode Conduction) ^a	1.7	A		
P_D	Power Dissipation ^a (T _A =25°C)	2.1	W		
	Power Dissipation ^a (T _A =70°C)	1.3	W		
$T_{\rm J}/T_{\rm STG}$	Operating Junction and Storage Temperature	-55 to +150	°C		

Thermal Resistance Ratings					
Symbol	Parameter Maximum Un				
$R_{\theta JA}$	Maximum Junction-to-Ambient ^a (t <= 10 sec)	62.5	°C/W		
	Maximum Junction-to-Ambient ^a (Steady-State)	110	C/W		

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250uA$	1			
Igss	Gate-Body Leakage	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			±100	nA
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			1 10	uA
I _{D(on)}	On-State Drain Current	$V_{DS} = 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	20			A
rDS (on)	Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 6.9 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 6.0 \text{ A}$			34 41	mΩ
gfs	Forward Tranconductance	$V_{DS} = 15 \text{ V}, I_D = 6.9 \text{ A}$		20		S
V _{SD}	Diode Forward Voltage	$I_S = 1.7 A$, $V_{GS} = 0 V$		0.77		V

Dyna mic ^b							
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units	
$Q_{\rm g}$	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_D = 6.9 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		4.0		nC	
Q_{gs}	Gate-Source Charge			1.1		nC	
Qgd	Gate-Drain Charge			1.4		nC	



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Dyna mic ^b							
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15 \ V \ , \ R_L = 1.9 \ \Omega \ ,$ $V_{GEN} = 10 \ V \ , \ I_D = 1 \ A$		12		ns	
$t_{\rm r}$	Rise Time			10		ns	
$t_{d(off)}$	Turn-Off Delay Time			60		ns	
tf	Fall Time			15		ns	
trr	Input Capacitance	$I_F = 1.7 \text{ A}$, $Di/Dt = 100 \text{ A/uS}$		50		ns	

NOTE:

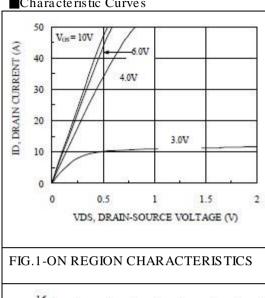
Pulse test: $PW \le 300us$ duty cycle $\le 2\%$.

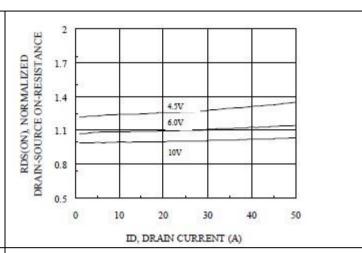
Guaranteed by design, not subject to production testing.



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■Characteristic Curves





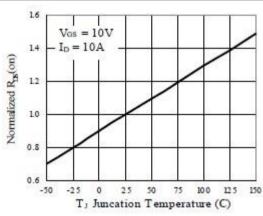


FIG.2- ON-RESISTANCE VARIATION WITH DRAIN CURRENT GATE VOLTAGE

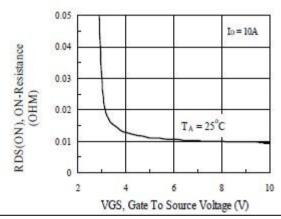


FIG.3-ON RESISTANCE VARIATION WITH **TEMPERATURE**

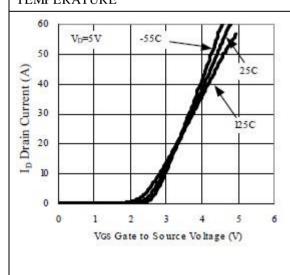


FIG.4-ON-RESISTANCE VARIATION WITH GATE TO SOURCE VOLTAGE

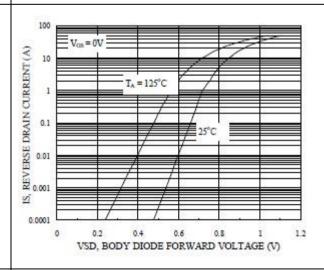


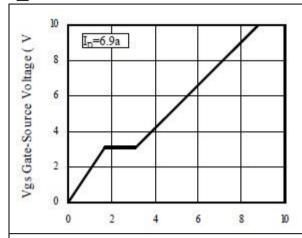
FIG.5-TRANSFER CHARACTERISTICS

FIG.6-BODY DIODE FORWARD VOLTAGE VARIATION WITH WOURCE CURRENT AND TEMPERATURE



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Characteristic Curves



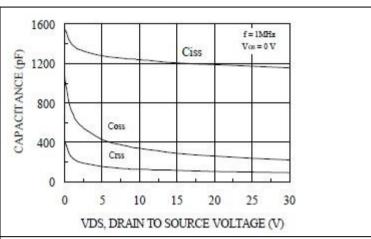


FIG.7-GATE CHARGE CHARACTERISTICS

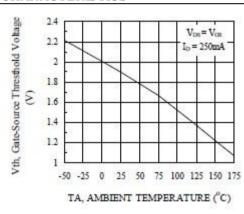


FIG.8-CAPACITANCE CHARACTERISTICS

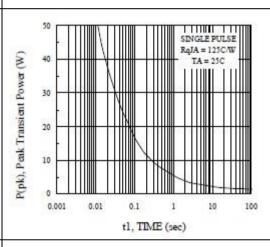


FIG.9-THRESHOLD VS AMBIENT TEMPERATURE

FIG.10-SINGLE PULSE MAXIMUM POWER DISSIPATION

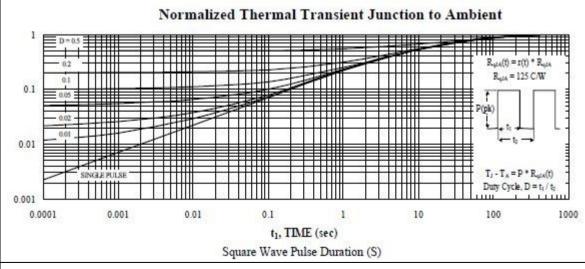


FIG.11-TRANSIENT THERMAL RESPONSE CURVE



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